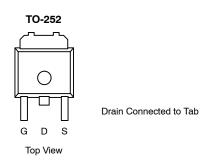


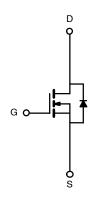
N-Channel 20-V (D-S)175 $^{\circ}$ C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A) ^a			
20	0.0045 @ V _{GS} = 4.5 V	100			
	0.006 @ V _{GS} = 2.5 V	90			

FEATURES

- TrenchFET® Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	20	V			
Gate-Source Voltage		V _{GS}	±15	v		
0.11. 0.10	T _C = 25°C		100			
Continuous Drain Current ^a	T _C = 100°C	l _D	80			
Pulsed Drain Current		I _{DM}	200	A		
Continuous Source Current (Diode Conduction) ^a		Is	65			
M. C. B. Britis	T _C = 25°C	5	71			
Maximum Power Dissipation	T _A = 25°C	P _D	8.3 ^{b, c}	— w		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
	t ≤ 10 sec.	R_{thJA}	15	18	°C/W		
Maximum Junction-to-Ambient ^b	Steady State		40	50			
Maximum Junction-to-Case		R _{thJC}	1.75	2.1			

Notes

- a. Package Limited
- b. Surface Mounted on 1" x 1" FR4 Board
- $c. \quad t \leq 10 \ \text{sec}$

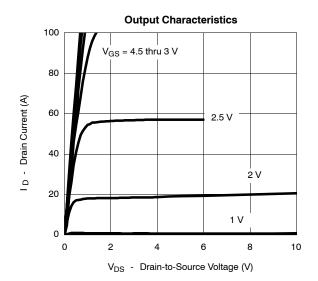


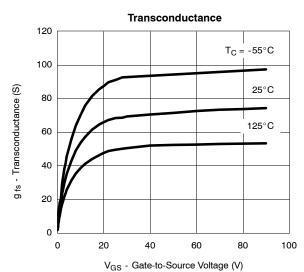
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit	
Static	· · · · · · · · · · · · · · · · · · ·		-	•			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 250 μA	20				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.5		1.5	V	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = \pm 12 V			±100	nA	
		V _{DS} = 20 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	DSS	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 125°C			50		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	100			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	0.		I	Ω	
Drain-Source On-State Resistanceb	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 20 A, T _J = 125°C		0.0055			
	'	V _{GS} = 2.5 V, I _D = 20 A		0.006			
Forward Transconductanceb	9fs	$V_{DS} = 5 \text{ V}, I_{D} = 40 \text{ A}$	20			S	
Dynamic ^a							
Input Capacitance	C _{iss}			3660			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$		730		pF	
Reverse Transfer Capacitance	C _{rss}			375			
Total Gate Charge ^c	Qg			26	35	nC	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 40 A		5			
Gate-Drain Charge ^c	Q _{gd}			7			
Gate Resistance	R _g		1		3.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			20	35		
Rise Time ^c	t _r	V_{DD} = 10 V, R_L = 0.25 Ω		120	190		
Turn-Off Delay Time ^c	t _{d(off)}	V_{DD} = 10 V, R_L = 0.25 Ω $I_D \cong$ 40 A, V_{GEN} = 4.5 V, R_G = 2.5 Ω		45	70	ns ns	
Fall Time ^c	t _f			20	35		
Source-Drain Diode Ratings an	d Characteristi	c (T _C = 25°C)					
Pulsed Current	I _{SM}				100	Α	
Diode Forward Voltage ^b	V _{SD}	I _F = 100 A, V _{GS} = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 40 A, di/dt = 100 A/μs		35	70	ns	

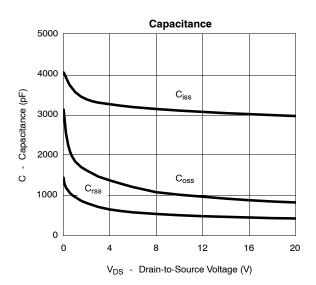
- Notes a. Guaranteed by design, not subject to production testing. b. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$. c. Independent of operating temperature.

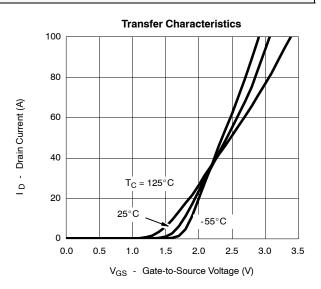


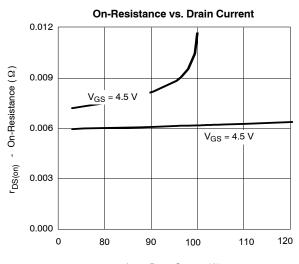
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

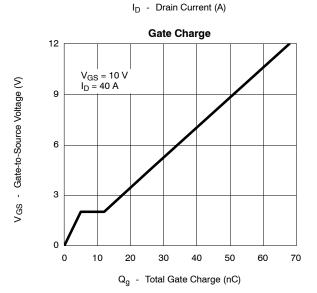






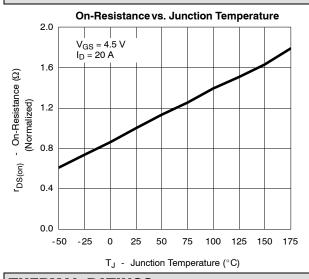


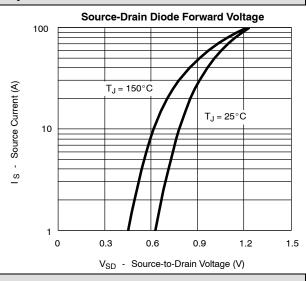




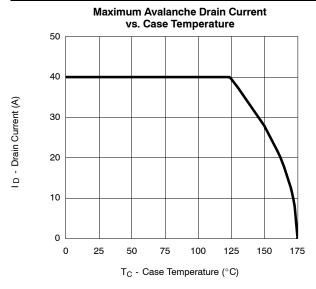


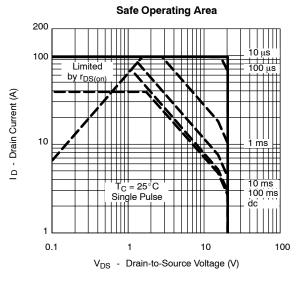
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

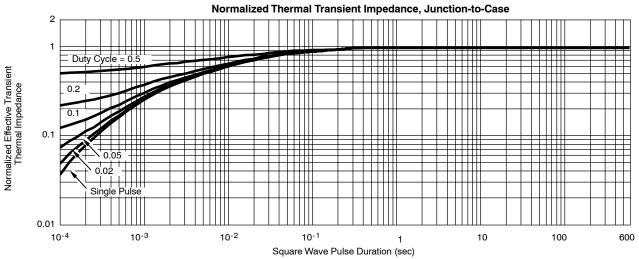




THERMAL RATINGS

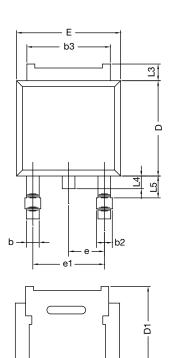


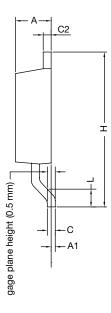






TO-252AA CASE OUTLINE





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	=	1.02	=	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

Note

• Dimension L3 is for reference only.

服务热线:400-655-8788

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